

**IN THE CLAIMS**

The following claim set replaces all prior versions, and listings, of claims in the application:

1.-57. Canceled.

58. (New) A gallium nitride based compound semiconductor light-emitting device comprising:

a semiconductor stacked structure including an n-type gallium nitride based compound semiconductor layer and a p-type gallium nitride based compound semiconductor layer;

a light-transmitting, first electrode, through which light can pass, provided over a surface of the p-type gallium nitride based compound semiconductor layer;

a second electrode for bonding, provided on a surface of the p-type gallium nitride based compound semiconductor layer, and electrically connected to the first electrode,

said second electrode contacting with the p-type gallium nitride based compound semiconductor layer and being adhered to the p-type gallium nitride based compound semiconductor layer stronger than a bond of the p-type gallium nitride based compound semiconductor layer with the first electrode or than a bond of the first electrode with the second electrode.